

7. (New) The method for forming a capacitor as claimed in claim 5, wherein the etching stop layer comprises silicon nitride.

REMARKS

With this amendment, claim 3 has been amended, claims 1, 2 and 4 have been cancelled, and claims 5-7 have been added.

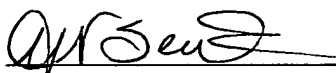
The specification has been amended to identify parent application no. 09/545,5459 and to include a claim of priority.

A copy of the original Declaration and Power of Attorney is submitted herewith pursuant to M.P.E.P. 201.06(c).

Applicants request prompt and favorable consideration by the Examiner of the now pending application.

Respectfully submitted,

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